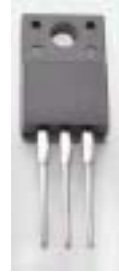


# IRF630F

N-channel mosfet transistor



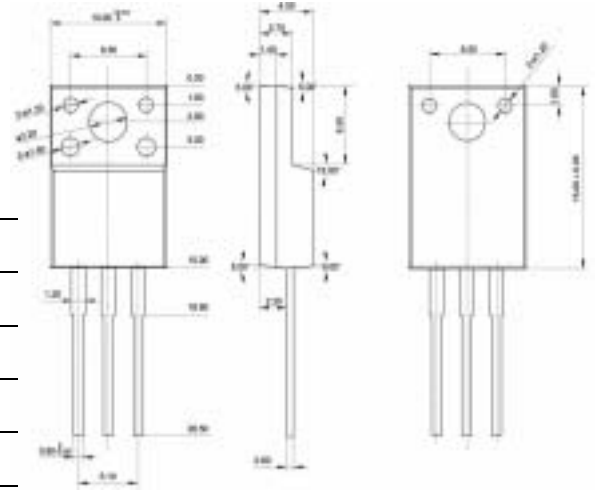
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## ◆ Features

- With TO-220F package
- Low on-state and thermal resistance
- Fast switching
- $V_{DSS}=200V$ ;  $R_{DS(ON)} 0.4$  ;  $I_D=9A$
- 1.gate 2.drain 3.source

## ◆ Absolute Maximum Ratings Tc=25

SYMBOL	PARAMETER	RATING	UNIT
$V_{DSS}$	Drain-source voltage ( $V_{GS}=0$ )	200	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25$	9	A
$P_{tot}$	Total Dissipation@TC=25	35	W
$T_j$	Operating Junction temperature	150	
$T_{stg}$	Storage temperature	-65~150	



TO-220F

## ◆ Electrical Characteristics Tc=25

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS}=0$ ; $I_D=0.25mA$	200		V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}$ ; $I_D=1mA$	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	$V_{GS}=10V$ ; $I_D=5.4A$		400	m
$I_{GSS}$	Gate source leakage current	$V_{GS}=\pm 20V$ ; $V_{DS}=0$		$\pm 100$	nA
$I_{DSS}$	Zero gate voltage drain current	$V_{DS}=200V$ ; $V_{GS}=0$		10	$\mu A$
$V_{SD}$	Diode forward voltage	$I_F=9A$ ; $V_{GS}=0$		1.2	V